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MOS FET

SK8603170L

Panasonic

SK8603170L

Silicon N-channel MOS FET

For Load-switching / For DC-DC Converter

■ Features

- Low Drain-source On-state Resistance : RDS(on)typ = $3.9 \text{ m}\Omega$ (VGS = 4.5 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : 17

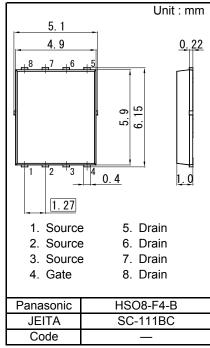
■ Packaging

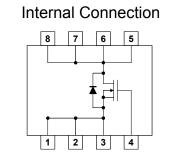
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter			Rating		Unit		
Drain to Source Voltage			30		V		
ate to Source Voltage			±20		V		
Ta = 25 °C, t = 10 s *1			28				
Ta = 25 °C, DC *1		ID	20		۸		
Tc = 25 °C			59		A		
Pulsed	d, Tch < 150 °C ^{*2}		84				
Total Power $Ta = 25 ^{\circ}\text{C}, DC^{*1}$ Dissipation $Tc = 25 ^{\circ}\text{C}$		DD	2.8	W			
		PD	24	۷V			
Thermal Resistance Ch		Rth(ch-a)	44		°C / W		
ance	Channel to Case	Rth(ch-c)	5.1 °C		-C / VV		
Channel Temperature		Tch	150				
Operating ambient temperature		Topr	-40 to	+85	°C		
Storage Temperature Range		Tstg	-55 to	+150			
Avalanche Current (Single pulse) *3		IAR	14		Α		
Avalanche Energy (Single pulse) *3		EAR	24		mJ		
	Voltag Voltag Ta = 2 Ta = 2 Tc = 2 Pulsec ance erature ent ten rature ent (Si	Voltage Voltage Ta = 25 °C, t = 10 s *1 Ta = 25 °C, DC *1 Tc = 25 °C Pulsed, Tch < 150 °C *2 Ta = 25 °C, DC *1 Tc = 25 °C Channel to Ambient Channel to Case erature ent temperature rature Range ent (Single pulse) *3	VoltageVDSVoltageVGSTa = 25 °C, t = 10 s *1 IDTa = 25 °C, DC *1 IDPulsed, Tch < 150 °C *2 PDTa = 25 °C, DC *1 PDTa = 25 °CPDanceChannel to Ambient Rth(ch-a) Channel to Case Rth(ch-c)eratureTchent temperatureToprrature RangeTstgent (Single pulse) *3 IAR	Voltage VDS 30 Voltage VGS ±20 Ta = 25 °C, t = 10 s *1 28 Ta = 25 °C, DC *1 1D 20 Tc = 25 °C 59 Pulsed, Tch < 150 °C *2	Voltage VDS 30 Voltage VGS ±20 Ta = 25 °C, t = 10 s *1 28 Ta = 25 °C, DC *1 20 For = 25 °C 59 Pulsed, Tch < 150 °C *2		

- Note *1 Device mounted on a glass-epoxy board in Figure 1
 - *2 Pulse test: Ensure that the channel temperature does not exceed 150 °C
 - *3 VDD = 24 V, VGS = 10 to 0 V, L = 0.1 mH, Tch = 25 $^{\circ}$ C (initial)





Pin Name

- 1. Source 5. Drain
- 2. Source 6. Drain
- 3. Source4. Gate7. Drain8. Drain



Figure 1 FR4 Glass-Epoxy Board 25.4 mm × 25.4 mm × 0.8 mm

Doc No. TT4-EA-14480 Revision. 2

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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			10	μΑ
Gate-source Leakage Current	IGSS	VGS = ± 16 V, VDS = 0 V			±10	μΑ
Gate-source Threshold Voltage		ID = 2.56 mA, VDS = 10 V	1.3		3	V
Drain-source On-state Resistance		ID = 14 A, VGS = 10 V		2.9	4.1	mΩ
Diani-source On-sidle Nesistance	RDS(on)2	ID = 14 A, VGS = 4.5 V	3.9	5.8	1115.2	

Dynamic Characteristics

By Hamile Gridiadionolio						
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V f = 1 MHz		2 100	2 940	
Output Capacitance	Coss			250	350	pF
Reverse Transfer Capacitance	Crss			180	290	
Turn-on Delay Time *1	td(on)	VDD = 15 V, VGS = 0 to 10 V		11		no
Rise Time *1	tr	ID = 14 A		10		ns
Turn-off Delay Time *1	td(off)	VDD = 15 V, VGS = 10 to 0 V		48		no
Fall Time *1	tf	ID = 14 A		7		ns
Total Gate Charge	Qg	VDD = 15 V VCS = 0 to 4 5 V		17		
Gate to Source Charge	Qgs	VDD = 15 V, VGS = 0 to 4.5 V ID = 14 A		6		nC
Gate to Drain Charge	Qgd	10 - 14 A		7		
Gate resistance	rg	f = 5 MHz		1.2	3	Ω

Body Diode Characteristic

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Diode Forward Voltage	VSD	IS = 14 A, VGS = 0 V		0.8	1.2	V

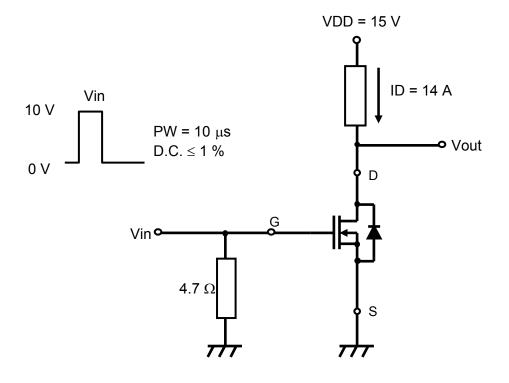
Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

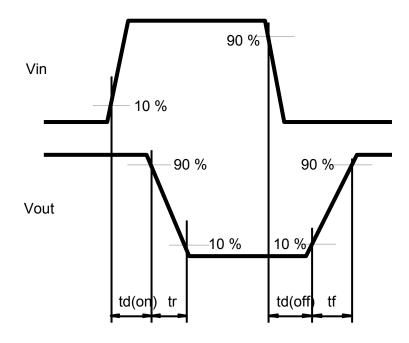
^{2. *1} Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

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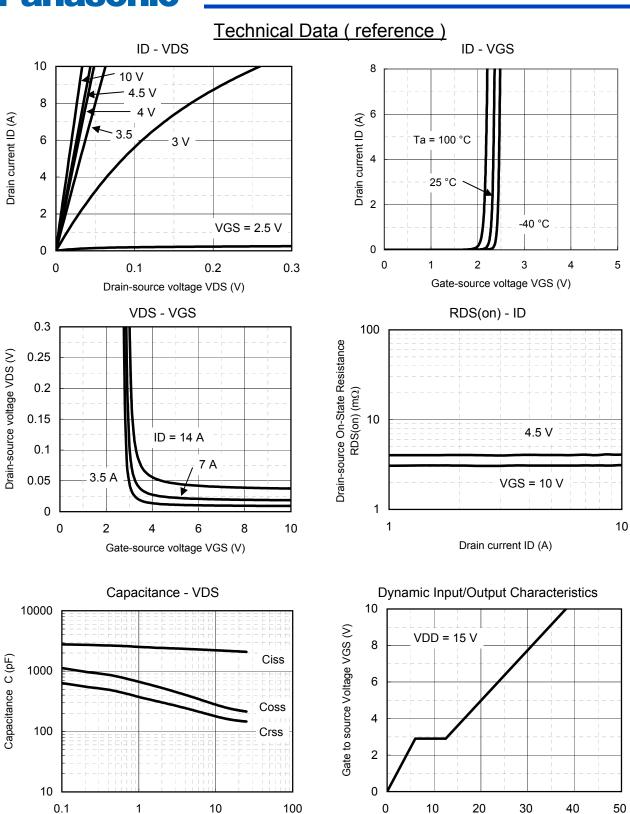
*1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time





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Total Gate Charge Qg (nC)

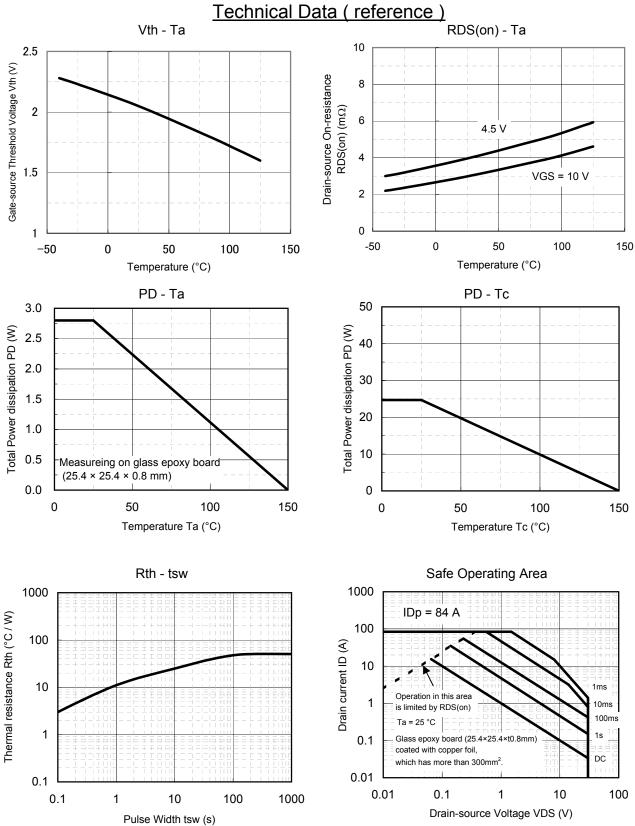
Established: 2012-12-20 Revised: 2013-05-31

Drain-source voltage VDS (V)

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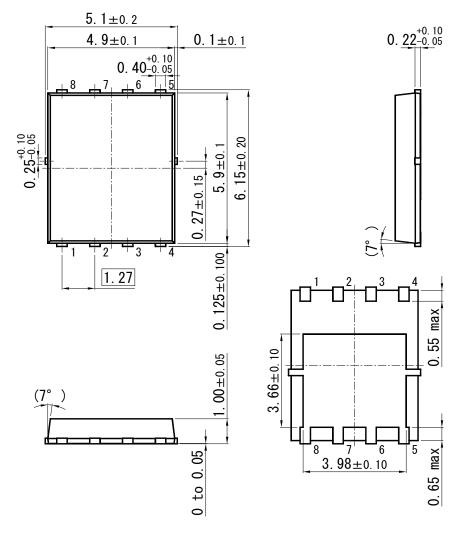
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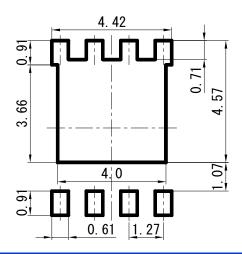
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HSO8-F4-B



■ Land Pattern (Reference) (Unit : mm)



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